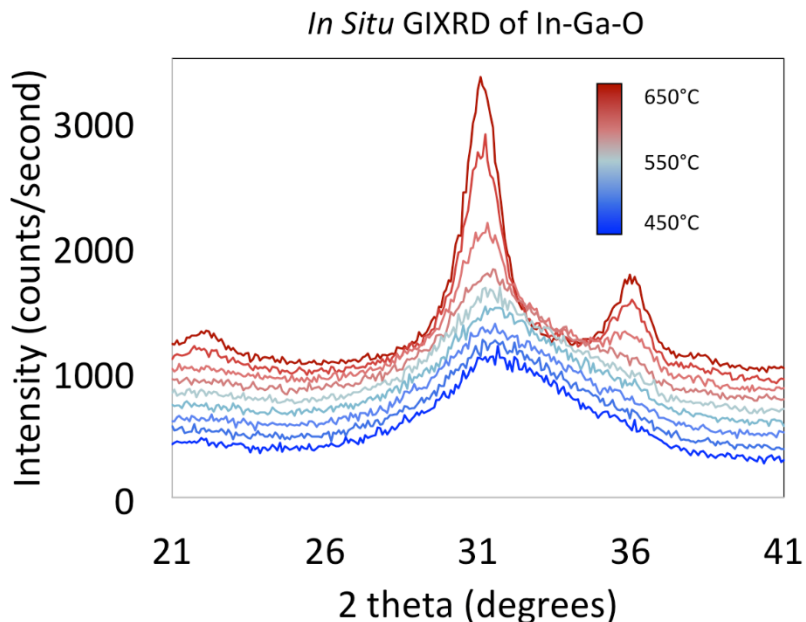


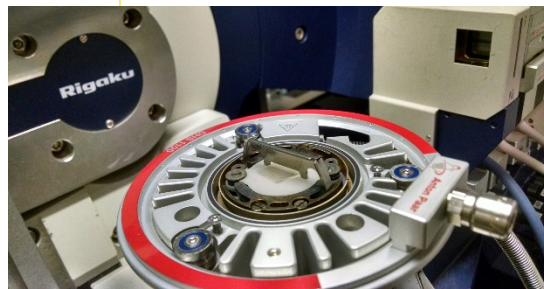
The Effect of Gallium

Exploration of Thermal Stability in Amorphous In-Ga-O

S. L. Moffitt, A. Falduto, X. Yan, Q. Ma, Q. Zhu, D. B. Buchholz, R. P. H. Chang, T. O. Mason, T. J. Marks, and M. J. Bedzyk
Materials Research Science & Engineering Center, Northwestern University



Amorphous indium oxide doped with gallium (a-IGO) is a model system to help develop the role of dopants in amorphous oxides. Gallium is well established in the literature as an important dopant but is usually studied as a member of multiple dopant systems where its role becomes convoluted.



Crystallization as a function of gallium level is monitored with X-rays as the process occurs on a heated stage